

# 2MBI900VXA-120E-54

**IGBT Modules** 

# **IGBT MODULE (V series)** 1200V / 900A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive

AC and DC Servo Drive Amplifier

Uninterruptible Power Supply

Industrial machines, such as Welding machines



#### Maximum Ratings and Characteristics

#### ● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Collector-E	Collector-Emitter voltage				1200	V	
Gate-Emitt	Gate-Emitter voltage				±20	V	
7	Collector current		Continuous	Tc=25°C	1200		
rter			Continuous	Tc=100°C	900		
Collector c			1ms		1800	A	
<b>=</b>					900		
			1ms		1800		
Collector power dissipation		Pc	1 device		5100	W	
Junction temperature		Tj			175		
Operating junction temperature (under switching conditions)		Tjop			150	°C	
Case temperature		Tc			150	C	
Storage temperature		Tstg			-40 ~ +150		
Isolation voltag	between terminal and copper base (*1)	) //	AC : 1min.		4000	VAC	
	between thermistor and others (*2)	Viso	AC . IIIIII.	AC . IIIIII.			
	Mounting	-	M5		6.0		
Screw torque (*	3) Main Terminals	-	M8		10.0	Nm	
	Sense Terminals	-	M4	M4			

 Note \*1: All terminals should be connected together during the test.

 Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

 Note \*3: Recommendable Value : Mounting
 3.0 ~ 6.0 Nm
 (M5)

 Recommendable Value : Main Terminals
 8.0 ~ 10.0 Nm
 (M8)

 Recommendable Value : Sense Terminals
 1.8 ~ 2.1 Nm
 (M4)

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#### • Electrical characteristics (at T<sub>j</sub>= 25°C unless otherwise specified)

Items		Symbolo	mbols Conditions			Characteristics		
		Symbols	Conditions	litions		typ.	max.	Units
	Zero gate voltage collector current	ICES	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V		-	-	8.0	mA
	Gate-Emitter leakage current	IGES	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	1600	nA
	Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 900mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	VCE (sat)	V <sub>GE</sub> = 15V Ic = 900A	Tj=25°C	-	1.85	2.30	V
		(terminal)		Tj=125°C	-	2.15	-	
		(*4)		Tj=150°C	-	2.20	-	
		V		Tj=25°C	-	1.75	2.20	
		V <sub>CE (sat)</sub>		Tj=125°C	-	2.05	-	
		(chip)		Tj=150°C	-	2.10	-	
	Internal gate resistance	R <sub>G (int)</sub>	-		-	1.19	-	Ω
	Input capacitance	Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	83	-	nF
	Turn-on time	ton	V <sub>cc</sub> = 600V	-	1000	-	nsec	
		t	Ic = 900A V <sub>GE</sub> = ±15V R <sub>G</sub> = 1.6Ω L <sub>s</sub> = 70nH		-	400		-
		tr (i)			-	150		-
	Turn-off time	toff			-	1200		-
		tr			-	150		-
	Forward on voltage	VF		Tj=25°C	-	1.90	2.35	
		(terminal)		Tj=125°C	-	2.05	-	]
		(*4)	$V_{GE} = 0V$	Tj=150°C	-	2.00	-	
		VF	IF = 900A	Tj=25°C	-	1.80	2.25	V
				Tj=125°C	-	1.95	-	
		(chip)		Tj=150°C	-	1.90	-	1
	Reverse recovery time	trr	I <sub>F</sub> = 900A		-	200	-	nsec
r	Desistance	D	T = 25°C		-	5000	-	0
	Resistance	R	T = 100°C		465	495	520	Ω
Ë	B value	В	T = 25/50°C		3305	3375	3450	K

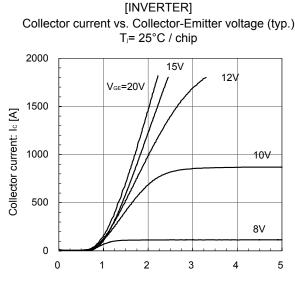
Note \*4: Fuji defined  $V_{\text{OE}}$  value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm. • Thermal resistance characteristics

Itomo	Symbols	Conditions	Characteristics			Units
Items		Conditions	min.	typ.	max.	Units
Thermal registeres (tdevice)	R <sub>th(j-c)</sub>	Inverter IGBT	-	-	0.030	°C/W
Thermal resistance(1device)		Inverter FWD	-	-	0.054	
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.00625	-	1

Note \*5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

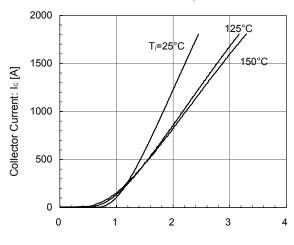
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#### Characteristics (Representative)



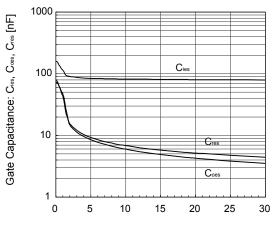
Collector-Emitter voltage: VCE [V]



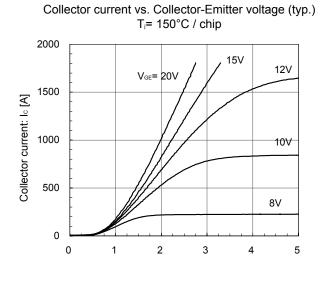


Collector-Emitter Voltage: VCE [V]

[INVERTER] Gate Capacitance vs. Collector-Emitter Voltage (typ.)  $V_{GE}$ = 0V, f = 1MHz, T<sub>i</sub>= 25°C

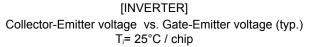


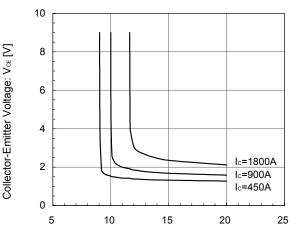
Collector-Emitter voltage: VCE [V]



[INVERTER]

Collector-Emitter voltage: VCE [V]





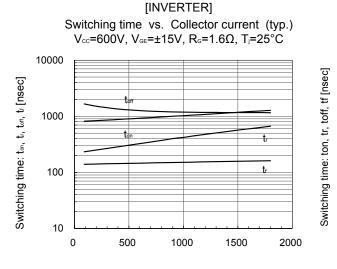
Gate-Emitter Voltage: VGE [V]

[INVERTER] Dynamic Gate Charge (typ.) Vcc=600V, Ic=900A, Tj= 25°C 1000 20 Collector-Emitter voltage: V œ [V] 750 15 Vce 10 500 5 250 0 0 VGE -5 -250 -10 -500 -15 -750 -1000 -20 -15000 -10000 -5000 0 5000 10000 15000

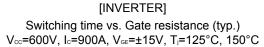
Gate charge: Q<sub>9</sub> [nC]

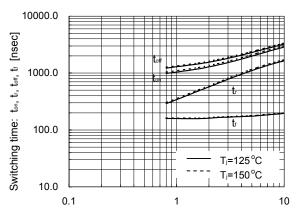
3

Gate-Emitter voltage: V<sub>GE</sub> [V]



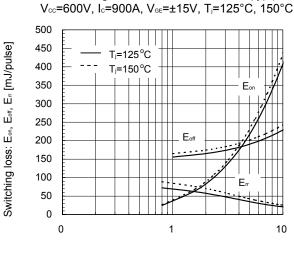
Collector current: Ic [A]



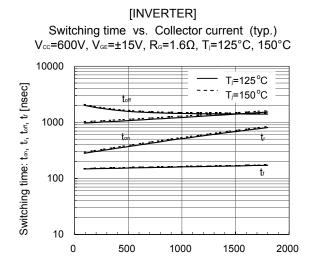


Gate resistance: R<sub>G</sub> [Ω]





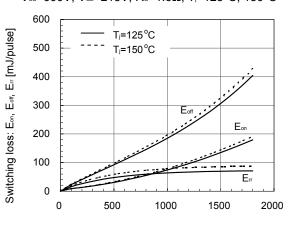
Gate resistance:  $R_G$  [ $\Omega$ ]



Collector current: Ic [A]



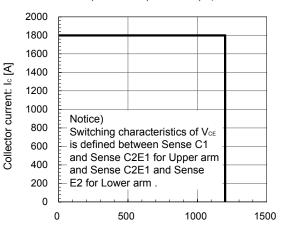
Switching loss vs. Collector current (typ.)  $V_{cc}$ =600V,  $V_{GE}$ =±15V,  $R_G$ =1.6 $\Omega$ , T<sub>i</sub>=125°C, 150°C



Collector current: Ic [A]

#### [INVERTER]

Reverse bias safe operating area (max.)  $+V_{GE}=15V, -V_{GE}=15V, R_{G}=1.6\Omega, T_{J}=150^{\circ}C$ 



Collector-Emitter voltage: VCE [V]

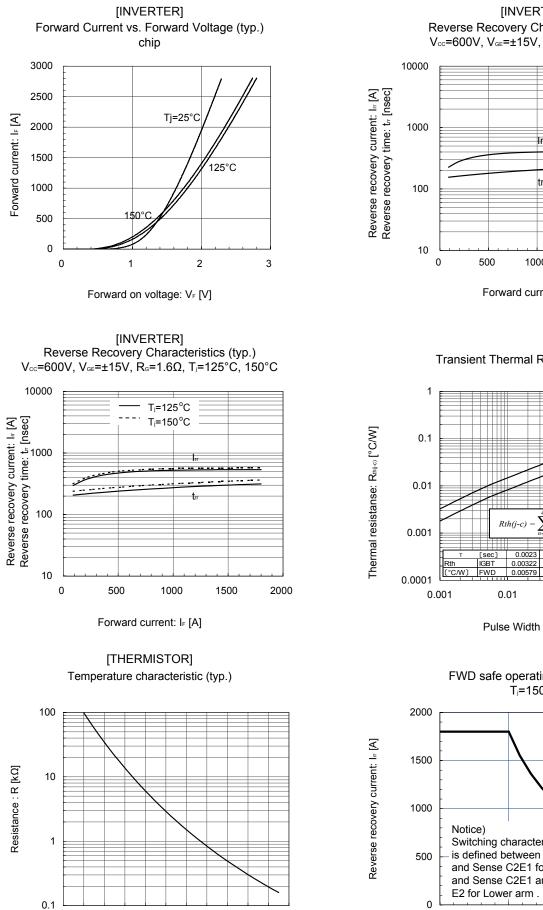
-60 -40 -20

0

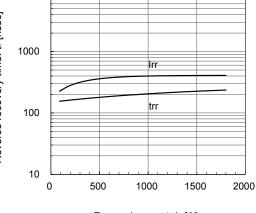
20 40

Temperature [°C]

60

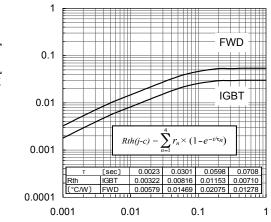


[INVERTER] Reverse Recovery Characteristics (typ.) Vcc=600V, VGE=±15V, RG=1.6Ω, TJ=25°C



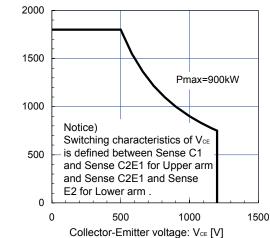
Forward current: IF [A]

Transient Thermal Resistance (max.)



Pulse Width : Pw [sec]

#### FWD safe operating area (max.) . Ti=150°℃

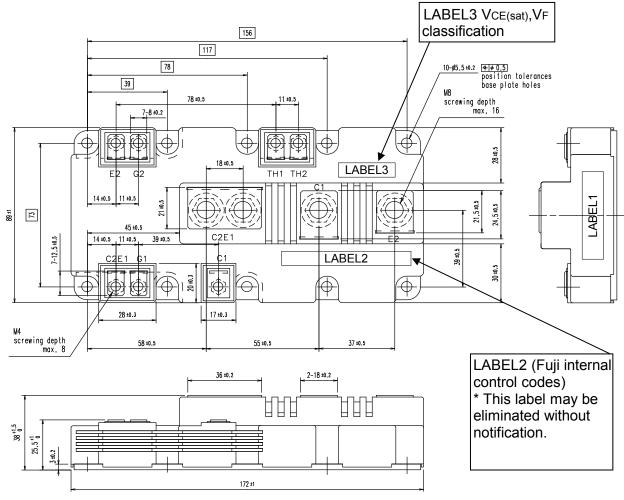


80 100 120 140 160

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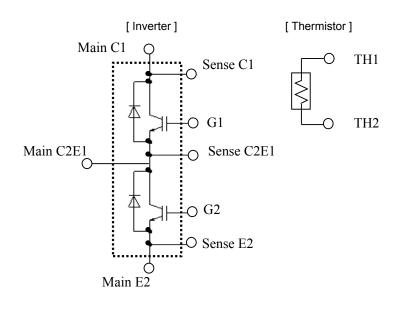
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#### Outline Drawings, mm

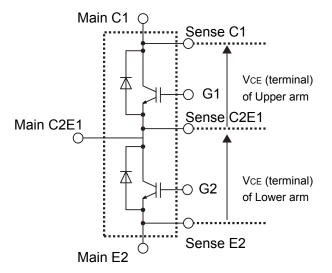


Weight:850g(typ.)

### Equivalent Circuit Schematic



#### Definition of on-state voltage at terminal and switching characteristics



Fuji defined VCE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Switching characteristics of VCE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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